

ESDS31x 数据线路浪涌和 ESD 保护二极管矩阵

1 特性

- IEC 61000-4-2 ESD 保护：
 - $\pm 30\text{kV}$ 接触放电
 - $\pm 30\text{kV}$ 空气间隙放电
- IEC 61000-4-4 EFT 保护：
 - 80A (5/50ns)
- IEC 61000-4-5 浪涌保护：
 - 25A (8/20 μs)
- IO 电容：
 - 4.5pF (典型值)
- 直流击穿电压：5.5V (最小值)
- 超低漏电流：5nA (典型值)
- 支持速率高达 5Gbps 的高速接口
- 工业温度范围：-40°C 至 +125°C
- 简易直通布线封装 (ESDS312)

2 应用

- 终端设备：
 - 以太网交换机
 - 接入点
 - 网关
 - 打印机
 - DVR 和 NVR
- 接口：
 - Ethernet™ 10/100/1000Mbps
 - USB™ 2.0
 - GPIO

3 说明

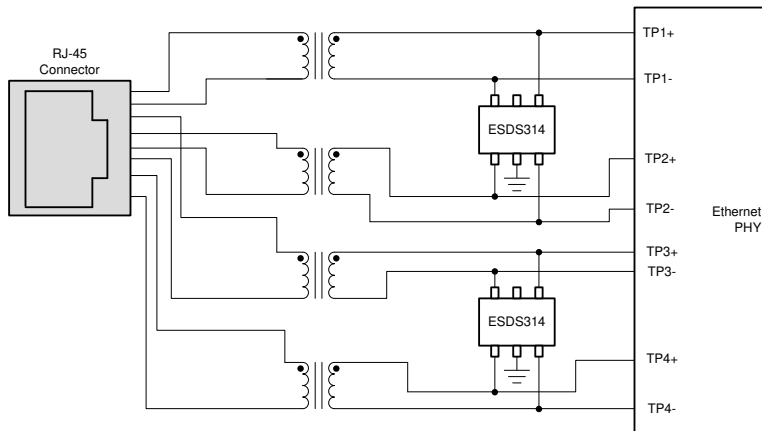
ESDS31x 器件是一种单向 TVS ESD 保护二极管阵列，用于高达 25A (8/20 μs) 的以太网、USB 和通用数据线路浪涌保护。ESDS31x 器件旨在耗散那些高于 IEC61000-4-2 国际标准 (4 级) 中规定的最高水平的 ESD 冲击。

这些器件具有每通道 4.5pF IO 电容，因此非常适用于保护 Ethernet 10/100/1000、USB 2.0 和 GPIO 等高速接口。低动态电阻和低钳位电压支持针对瞬态事件提供系统级保护。

封装信息

器件型号	通道数	封装 ⁽¹⁾
ESDS311	1 通道	DYF (SOD323, 2)
ESDS312	2 通道	DBV (SOT-23, 5)
ESDS314	4 通道	DBV (SOT-23, 5)

(1) 如需更多信息，请参阅节 10



典型应用原理图



Table of Contents

1 特性.....	1	6.4 Device Functional Modes.....	8
2 应用.....	1	7 Application and Implementation.....	9
3 说明.....	1	7.1 Application Information.....	9
4 Pin Configuration and Functions.....	2	7.2 Typical Application.....	9
5 Specifications.....	4	7.3 Power Supply Recommendations.....	10
5.1 Absolute Maximum Ratings.....	4	7.4 Layout.....	10
5.2 ESD Ratings - JEDEC Specifications.....	4	8 Device and Documentation Support.....	12
5.3 ESD Ratings - IEC Specifications.....	4	8.1 Documentation Support.....	12
5.4 Recommended Operating Conditions.....	4	8.2 接收文档更新通知.....	12
5.5 Thermal Information.....	4	8.3 支持资源.....	12
5.6 Electrical Characteristics.....	5	8.4 Trademarks.....	12
5.7 Typical Characteristics.....	6	8.5 静电放电警告.....	12
6 Detailed Description.....	8	8.6 术语表.....	12
6.1 Overview.....	8	9 Revision History.....	12
6.2 Functional Block Diagram.....	8	10 Mechanical, Packaging, and Orderable Information.....	13
6.3 Feature Description.....	8		

4 Pin Configuration and Functions

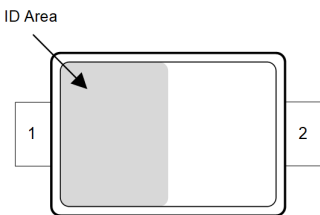


图 4-1. ESDS311 DYF, 2-Pin SOD323 (Top View)

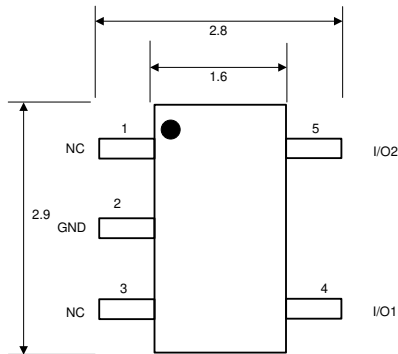


图 4-2. ESDS312 DBV Package, 5-Pin SOT23 (Top View)

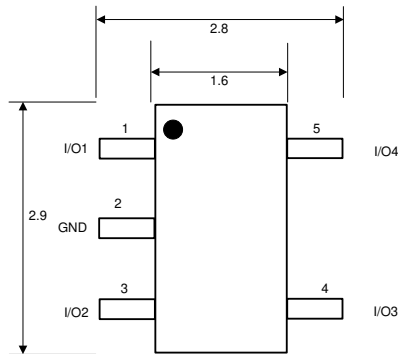


图 4-3. ESDS314 DBV Package, 5-Pin SOT23 (Top View)

表 4-1. Pin Functions for ESDS311

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
I/O	1	I/O	Surge/ESD protected channels. Connect to the lines being protected.
GND	2	GND	Ground. Connect to ground.

表 4-2. Pin Functions for ESDS312

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
I/O1	4	I/O	Surge/ESD protected channels. Connect to the lines being protected.
I/O2	5		
GND	2	GND	Ground. Connect to ground.
NC	1	NC	Not connected; Used for optional straight-through routing. Can be left floating or grounded
NC	3		

表 4-3. Pin Functions for ESDS314

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
I/O1	1	I/O	Surge/ESD protected channels. Connect to the lines being protected.
I/O2	3		
I/O3	4		
I/O4	5		
GND	2	GND	Ground. Connect to ground

(1) I = input, O = output, NC = no connection, and GND = ground

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
IEC 61000-4-4 Electrical Fast Transient	Peak Power at 25 °C		80	A
IEC 61000-4-5 Surge (t _p 8/20μs)	Peak Power at 25 °C		170	W
	Peak Current at 25 °C		25	A
T _A	Operating free-air temperature	- 40	125	°C
T _{stg}	Storage temperature	- 65	155	°C

- (1) Operation outside the *Absolute Maximum Rating* may cause permanent device damage. *Absolute Maximum Rating* do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Condition*. If used outside the *Recommended Operating Condition* but within the *Absolute Maximum Rating*, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

5.2 ESD Ratings - JEDEC Specifications

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all-pins ⁽¹⁾	±2500	V
		Charged device model (CDM), per JEDEC specification JESD22-C101, all pins ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 ESD Ratings - IEC Specifications

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	IEC 61000-4-2 Contact Discharge, all pins	±30000	V
		IEC 61000-4-2 Air Discharge, all pins	±30000	

5.4 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{IN}	Input voltage	0		3.6	V
T _A	Operating Free Air Temperature	- 40		125	°C

5.5 Thermal Information

THERMAL METRIC ⁽¹⁾		ESDS311	ESDS312	ESDS314	UNIT
		DYF (SOD323)	DBV (SOT-23)	DBV (SOT-23)	
		2 PINS	5 PINS	5 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	739.2	163.9	127.6	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	287.7	113.4	78.9	°C/W
R _{θJB}	Junction-to-board thermal resistance	605.5	76.9	43.9	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	118.4	59.8	24.5	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	591.1	76.8	43.7	°C/W

5.5 Thermal Information (续)

THERMAL METRIC ⁽¹⁾		ESDS311	ESDS312	ESDS314	UNIT
		DYF (SOD323)	DBV (SOT-23)	DBV (SOT-23)	
		2 PINS	5 PINS	5 PINS	
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

5.6 Electrical Characteristics

At $T_A = 25^\circ\text{C}$ unless otherwise noted

PARAMETER		TEST CONDITIONS	Device	MIN	TYP	MAX	UNIT
V_{RWM}	Reverse stand-off voltage	$I_{IO} < 500\text{nA}$, across operating temperature range				3.6	V
$I_{LEAKAGE}$	Leakage current at 3.6V	$V_{IO} = 3.6\text{V}$, Any IO pin to GND			5	50	nA
V_{BRF}	Breakdown voltage, IO to GND ⁽¹⁾	$I_{IO} = 1\text{mA}$		4.5		7.5	V
V_{FWD}	Forward Voltage, GND to IO	$I_{IO} = 1\text{mA}$			0.8		V
V_{HOLD}	Holding Voltage, IO to GND ⁽²⁾	$I_{IO} = 1\text{mA}$			5		V
V_{CLAMP}	Surge Clamping voltage, $t_p = 8/20\mu\text{s}$	$I_{PP} = 1\text{A}$, Any IO pin to GND	ESDS312/314		5		V
V_{CLAMP}		$I_{PP} = 12\text{A}$, Any IO pin to GND	ESDS311		6.3		V
			ESDS312/314		5.6		
V_{CLAMP}		$I_{PP} = 25\text{A}$, Any IO pin to GND	ESDS311		7.7		V
			ESDS312/314		6.5		
V_{CLAMP}		$I_{PP} = 1\text{A}$, GND to any IO pin	ESDS312/314		1		V
V_{CLAMP}		$I_{PP} = 12\text{A}$, GND to any IO pin	ESDS311		3		V
			ESDS312/314		2.1		
V_{CLAMP}		$I_{PP} = 25\text{A}$, GND to any IO pin	ESDS311		4.9		V
			ESDS312/314		3.6		
V_{CLAMP}	TLP Clamping Voltage, $t_p = 100\text{ns}$	$I_{PP} = 16\text{A}$, Any IO pin to GND	ESDS311		6.5		V
			ESDS312/314		5.5		
V_{CLAMP}		$I_{PP} = 16\text{A}$, GND to any IO pin	ESDS311		3.4		V
			ESDS312/314		2.2		
C_{LINE}	Line capacitance, Any IO to GND	$V_{IO} = 0\text{V}$, $V_{p-p} = 30\text{mV}$, $f = 1\text{MHz}$			4.5	5.5	pF
ΔC_{LINE}	Variation of line capacitance	$C_{LINE1} - C_{LINE2}$, $V_{IO} = 0\text{V}$, $V_{p-p} = 30\text{mV}$, $f = 1\text{MHz}$	ESDS312/314		0.05	0.1	pF
C_{CROSS}	Line-to-line capacitance	$V_{IO} = 0\text{V}$, $V_{rms} = 30\text{mV}$, $f = 1\text{MHz}$	ESDS312/314		2.25	2.75	pF

(1) V_{BRF} and V_{BRR} are defined as the voltage obtained at 1mA when sweeping the voltage up, before the device latches into the snapback state

(2) V_{HOLD} is defined as the voltage when 1mA is applied, after the device has successfully latched into the snapback state.

5.7 Typical Characteristics

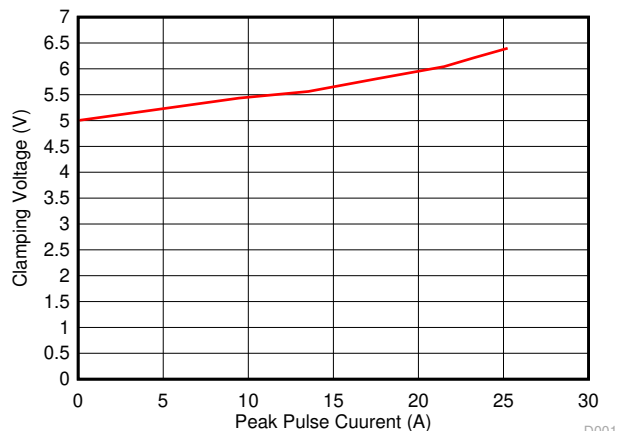


图 5-1. Clamping Voltage vs. Peak Pulse Current ($t_p = 8/20\mu s$), Any IO Pin to GND

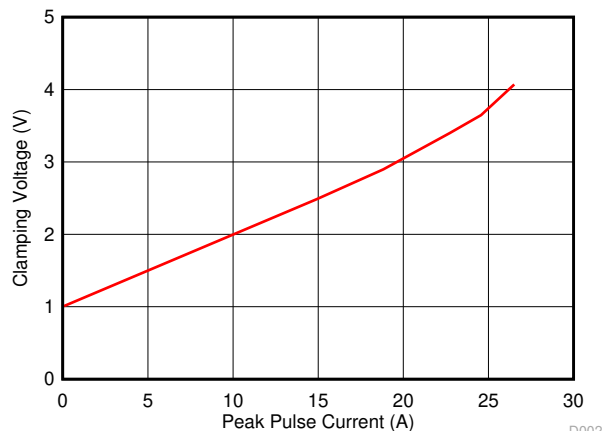


图 5-2. Clamping Voltage vs. Peak Pulse Current ($t_p = 8/20\mu s$), GND to Any IO Pin

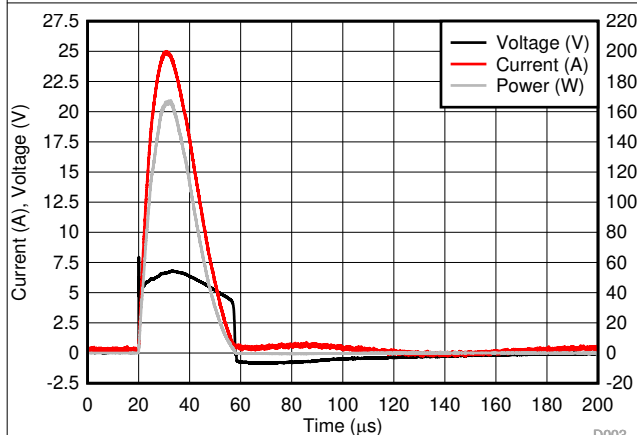


图 5-3. Surge Current, Clamping Voltage and Power Curve ($t_p = 8/20\mu s$), Any IO Pin to GND

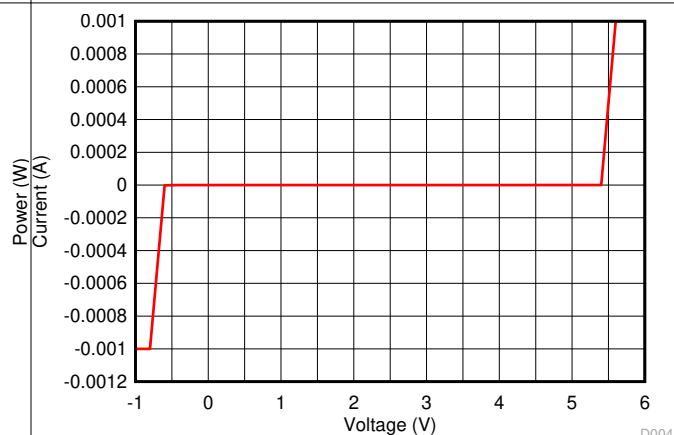


图 5-4. DC I-V Curve

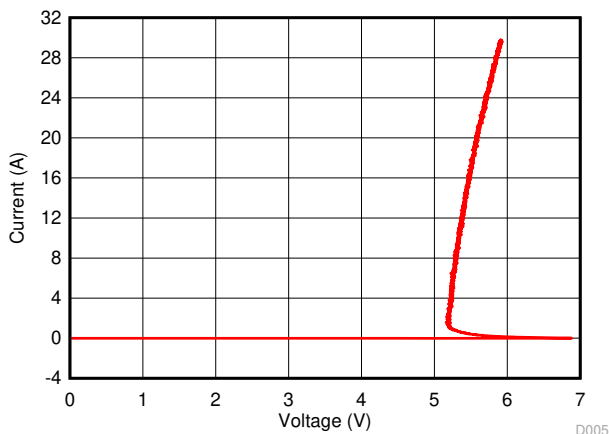


图 5-5. TLP I-V Curve, IO to GND, $t_p = 100ns$

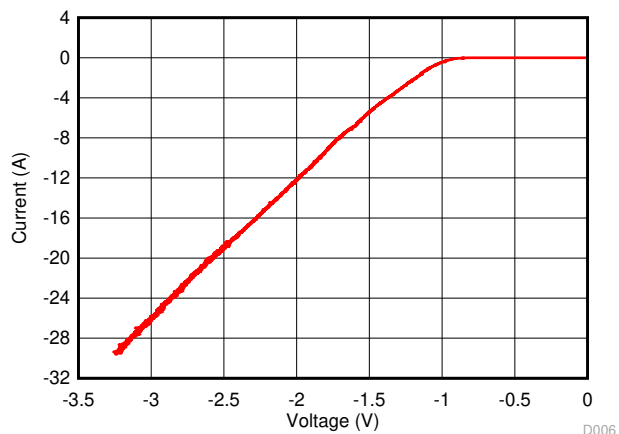
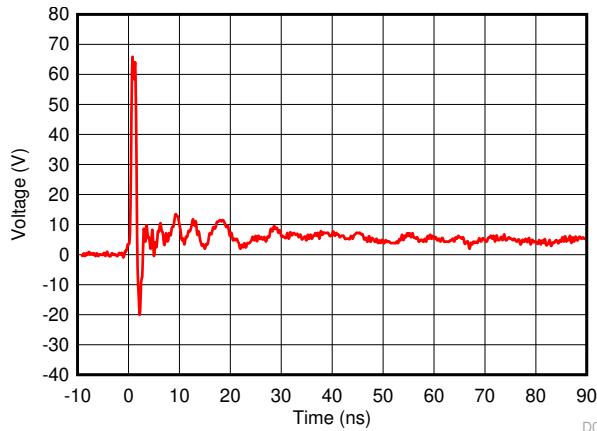


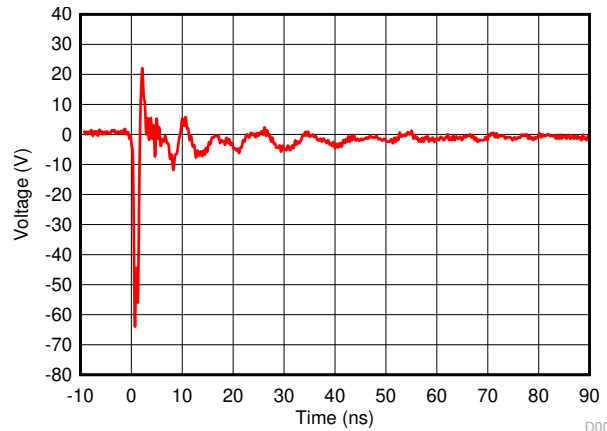
图 5-6. TLP I-V Curve, IO to GND Negative, $t_p = 100ns$



D007

D007_IEC_Pos.grf

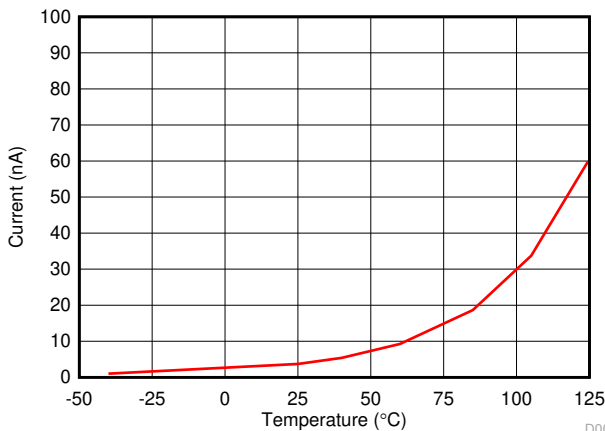
图 5-7. +8kV IEC 61000-4-2 Clamping Voltage Waveform



D008

D008_IEC_Neg.grf

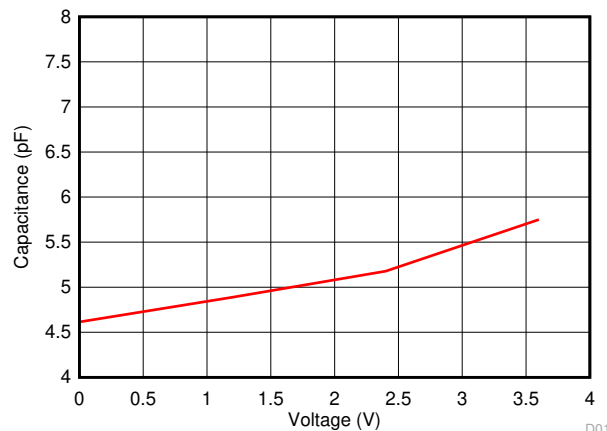
图 5-8. -8kV IEC 61000-4-2 Clamping Voltage Waveform



D009

D009_Leakage.grf

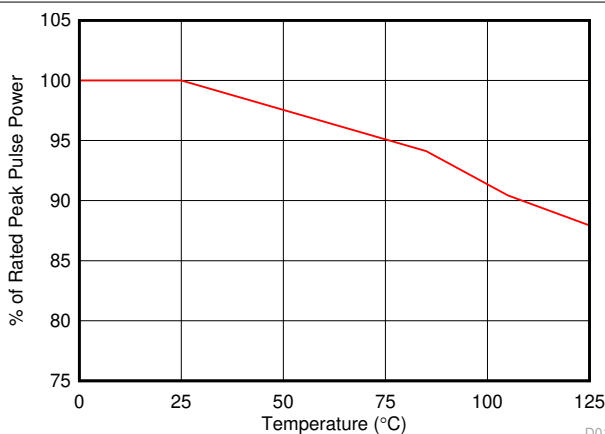
图 5-9. DC Leakage vs. Ambient Temperature, Bias Voltage = 3.6V



D010

D010_Cap_Vbias.grf

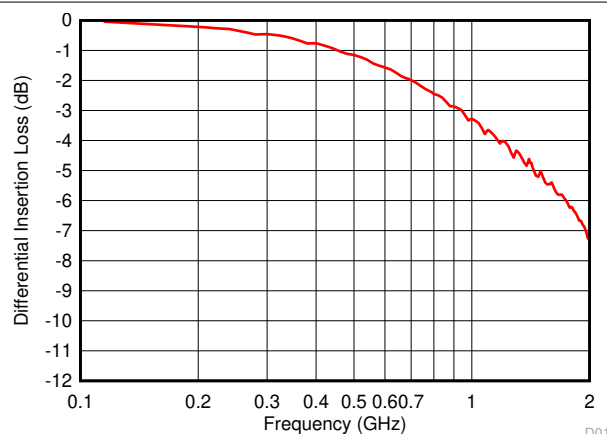
图 5-10. Capacitance vs. Bias Voltage at 25 °C



D011

D011_Power_Derating.grf

图 5-11. Surge Power Derating with Respect To Ambient Temperature



D012

D012_S21.grf

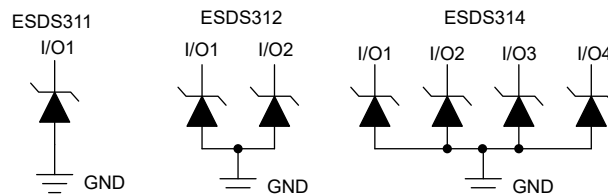
图 5-12. Differential Insertion Loss

6 Detailed Description

6.1 Overview

The ESDS31x devices are unidirectional ESD Protection Diodes with a low capacitance. These devices can dissipate high surge currents up to 25A (8/20 μ s) and ESD strikes above the maximum level specified by the IEC 61000-4-2 International Standard. The low capacitance makes this device an excellent choice for protecting high-speed signal interfaces such as Ethernet 10/100/1000Mbps and general purpose high speed data lines.

6.2 Functional Block Diagram



6.3 Feature Description

6.3.1 IEC 61000-4-4 EFT Protection

The I/O pins of ESDS311, ESDS312, and ESDS314 can withstand surge events (IEC 61000-4-5, 8/20 μ s waveform) up to 25A and 170W. These devices also provide ESD protection up to ± 30 kV contact and ± 30 kV air gap per IEC 61000-4-2 standard. The I/O pins can withstand an electrical fast transient (EFT) burst of up to 80A (IEC 61000-4-4 5/50ns waveform, 4kV with 50 Ω impedance). The capacitance between each I/O pin to ground is 4.5pF (typical) and 5.5pF (maximum). This device supports data rates up to 1Gbps.

The reverse DC breakdown voltage of each I/O pin is a minimum of 4.5V. This ensures that sensitive equipment is protected from surges above the reverse standoff voltage of 3.6V. The I/O pins feature an ultra-low leakage current of 100nA (maximum) with a bias of 3.6V. This device features an industrial operating range of -40°C to $+125^{\circ}\text{C}$.

6.4 Device Functional Modes

The ESDS31x devices are a passive integrated circuit that triggers when voltages are above V_{BRF} or below 0.7V. During ESD events, voltages as high as ± 30 kV (air) can be directed to ground via the internal diode network. When the voltages on the protected line fall below the trigger levels of ESDS31x (usually within a few nanoseconds) the devices reverts to passive.

7 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

7.1 Application Information

The ESDS31x devices are a diode type TVS which is used to provide a path to ground for dissipating surge and ESD events on high-speed signal lines between a human interface connector and a system. As the current from surge or ESD passes through the TVS, only a small voltage drop is present across the diode. This is the voltage presented to the protected IC. The low R_{DYN} of the triggered TVS holds this voltage, V_{CLAMP} , to a safe level for the protected IC.

7.2 Typical Application

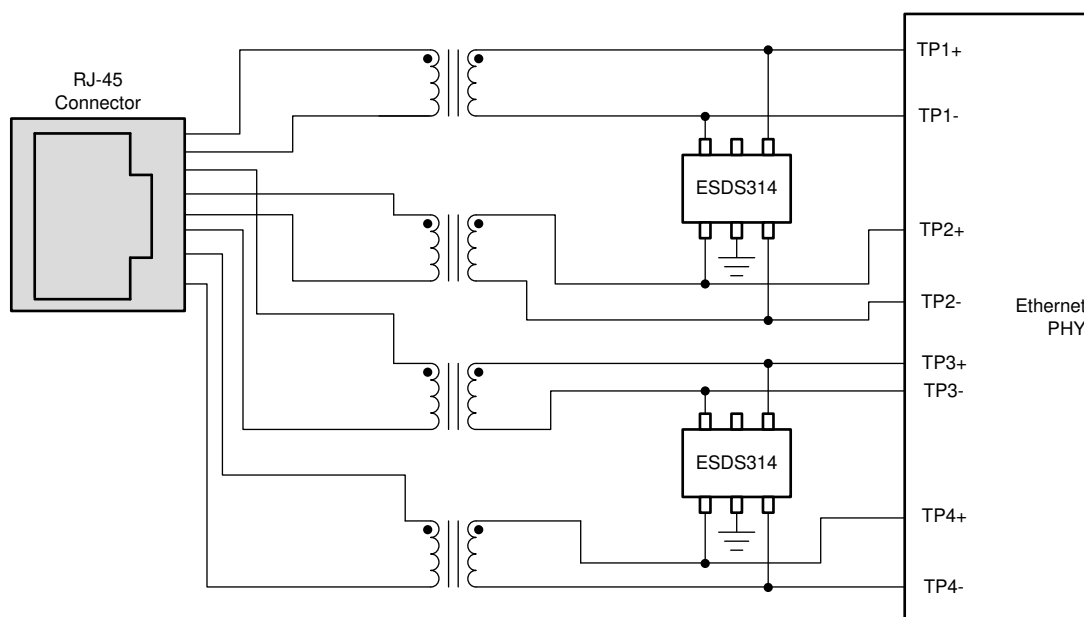


图 7-1. ESDS314 Protecting the Ethernet 1Gbps Interface

7.2.1 Design Requirements

A typical operation for the ESDS314 would be protecting a high speed dataline similar to one shown in 图 7-1. In this example, the ESDS314 is protecting an Ethernet PHY's data lines that has a nominal operating voltage of 3.6V. Many of the Ethernet interfaces that connect to long cables require protection against $\pm 1\text{kV}$ surge test through a $42\ \Omega$ coupling resistor and a $0.5\ \mu\text{F}$ capacitor, equaling roughly 24A of surge current. Without any input protection, if a surge event is caused by lightning, coupling, ringing, or any other fault condition, this input voltage will rise to hundreds of volts for multiple microseconds, harming the device.

For Ethernet 1000Base-T (1Gbps), application design parameters listed in 表 7-1 are known.

表 7-1. Design Parameters

DESIGN PARAMETER	VALUE
Signal range on differential data line pairs	0 to 3.6V
Operating frequency	125MHz

7.2.2 Detailed Design Procedure

7.2.2.1 Signal Range

The ESDS314 has 4 identical surge protection channels with each channel supporting a signal range of 0 to 3.6V. The device will work well with any Ethernet PHY that drives the single ended voltage on the data line up to a 3.6V.

7.2.2.2 Operating Frequency

The ESDS314 has a capacitance of 4.5pF (typical) and can support the 125MHz operation of Ethernet 1000Base-T application

7.2.3 Application Curves

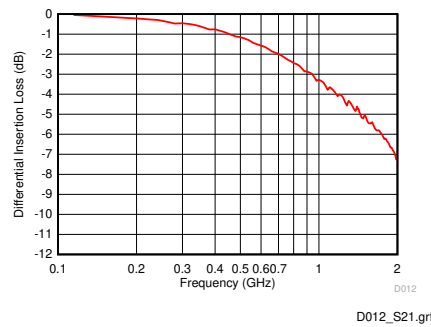


图 7-2. Differential Insertion Loss vs. Frequency

7.3 Power Supply Recommendations

The ESDS314, ESDS312 devices are passive ESD devices and there is no need to power it. Take care not to violate the recommended I/O specification (0 V to 3.6 V) to ensure the device functions properly.

7.4 Layout

7.4.1 Layout Guidelines

- The optimum placement is as close to the connector as possible.
 - EMI during an ESD event can couple from the trace being struck to other nearby unprotected traces, resulting in early system failures.
 - The PCB designer must minimize the possibility of EMI coupling by keeping any unprotected traces away from the protected traces which are between the TVS and the connector.
- Route the protected traces as straight as possible.
- Eliminate any sharp corners on the protected traces between the TVS and the connector by using rounded corners with the largest radii possible.
 - Electric fields tend to build up on corners, increasing EMI coupling.

7.4.2 Layout Example

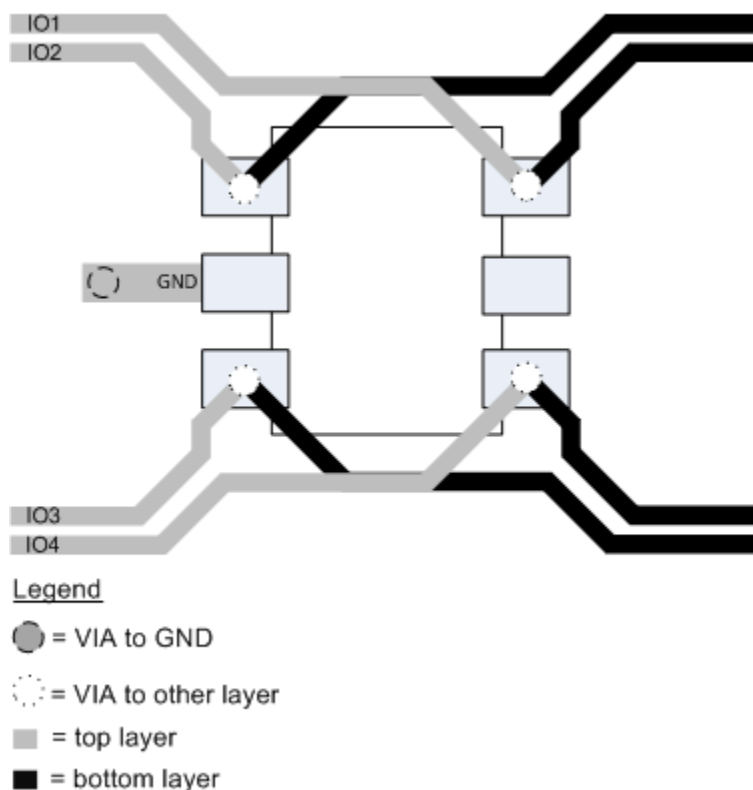


图 7-3. Layout Example for 4-channel Device

8 Device and Documentation Support

8.1 Documentation Support

8.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [TI's IEC 61000-4-x Testing application note](#)
- Texas Instruments, [ESD Layout Guide user's guide](#)
- Texas Instruments, [ESD Protection Diodes EVM user's guide](#)
- Texas Instruments, [Generic ESD Evaluation Module user's guide](#)
- Texas Instruments, [Reading and Understanding an ESD Protection Data Sheet user's guide](#)

8.2 接收文档更新通知

要接收文档更新通知，请导航至 [ti.com](https://www.ti.com) 上的器件产品文件夹。点击 [通知](#) 进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

8.3 支持资源

[TI E2E™ 中文支持论坛](#) 是工程师的重要参考资料，可直接从专家处获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题，获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [使用条款](#)。

8.4 Trademarks

Ethernet™ is a trademark of Xerox Corporation.

USB™ is a trademark of USB Implementers Forum.

TI E2E™ is a trademark of Texas Instruments.

所有商标均为其各自所有者的财产。

8.5 静电放电警告



静电放电 (ESD) 会损坏这个集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

8.6 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

9 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision B (September 2018) to Revision C (February 2024)	Page
• 更新了整个文档中的表、图和交叉参考的编号格式.....	1
• 在数据表中添加了 ESDS311 器件.....	1

Changes from Revision A (July 2018) to Revision B (September 2018)	Page
• 将“预告信息”更改为“量产数据”.....	1

Changes from Revision * (May 2018) to Revision A (July 2018)	Page
• 从“产品预发布”更改为“预告信息”	1

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
ESDS311DYFR	Active	Production	SOT (DYF) 2	3000 LARGE T&R	Yes	SN	Level-3-260C-168 HR	-40 to 125	37OF
ESDS311DYFR.B	Active	Production	SOT (DYF) 2	3000 LARGE T&R	Yes	SN	Level-3-260C-168 HR	-40 to 125	37OF
ESDS312DBVR	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	1R4B
ESDS312DBVR.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	-	Call TI	Call TI	-40 to 125	
ESDS314DBVR	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	1R2B
ESDS314DBVR.B	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	-	Call TI	Call TI	-40 to 125	

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ESDS311DYFR	SOT	DYF	2	3000	178.0	9.5	1.48	3.3	1.25	4.0	8.0	Q1
ESDS312DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
ESDS314DBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ESDS311DYFR	SOT	DYF	2	3000	210.0	200.0	42.0
ESDS312DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
ESDS314DBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0



SOT-23 - 1.45 mm max height

Front View:

- Overall dimensions: 3.0 x 2.6
- Pin locations: 1, 2, 3, 4, 5
- Dimensions: 1.75, 1.45, 1.9, 3.05, 2.75
- Feature table:

$\oplus$	0.2	$\odot$	C	A	B
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- Feature table header: 5X 0.5, 0.3
- Feature table body: 2X 0.95, 1.9
- Feature table footer: 0.15, 0.00

Side View:

- Chamfer: 4X 0°-15°
- Dimension: 0.15 TYP

End View:

- Chamfer: 4X 4°-15°
- Dimension: 0.22 TYP

Notes:

- NOTE 5: Points to a feature on the front view.

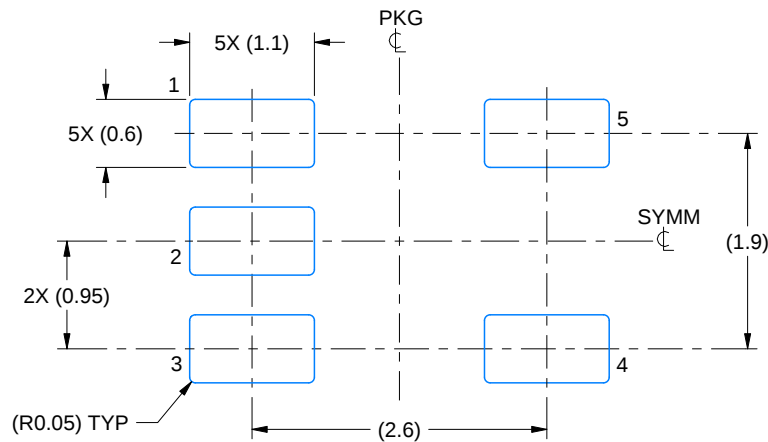
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
5. Support pin may differ or may not be present.

EXAMPLE BOARD LAYOUT

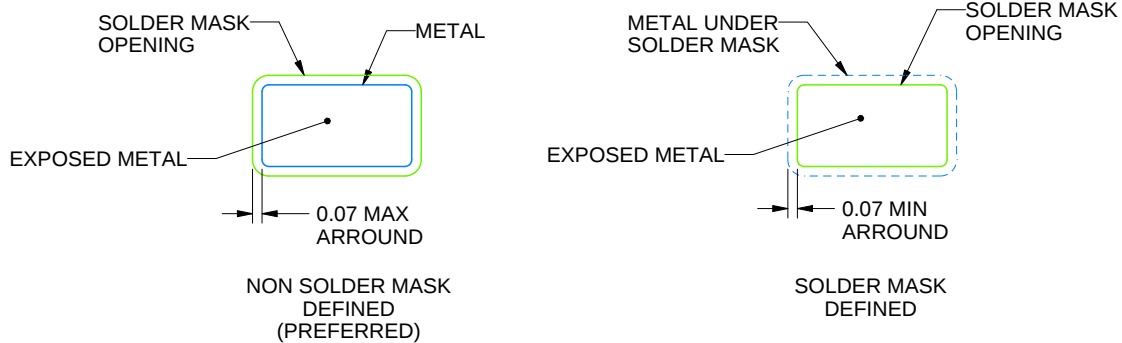
DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/K 08/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

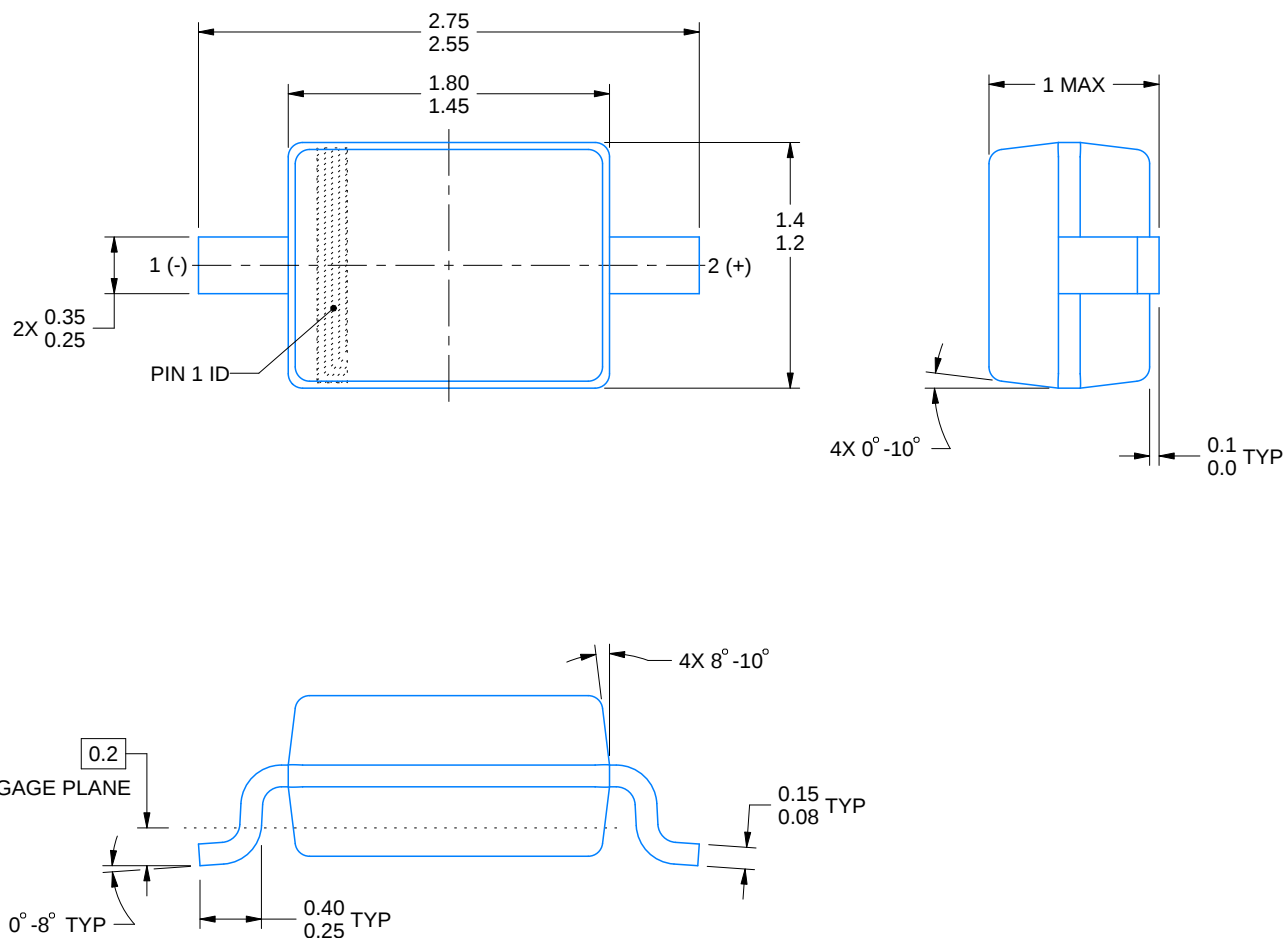
DYF0002A



PACKAGE OUTLINE

SOT(SOD-323) - 1 mm max height

SMALL OUTLINE TRANSISTOR



4228484/C 12/2024

NOTES:

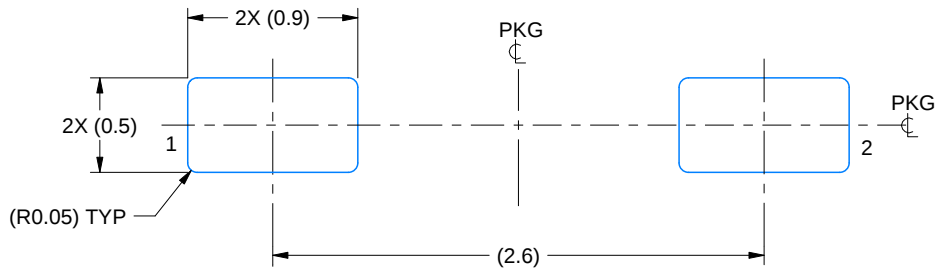
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

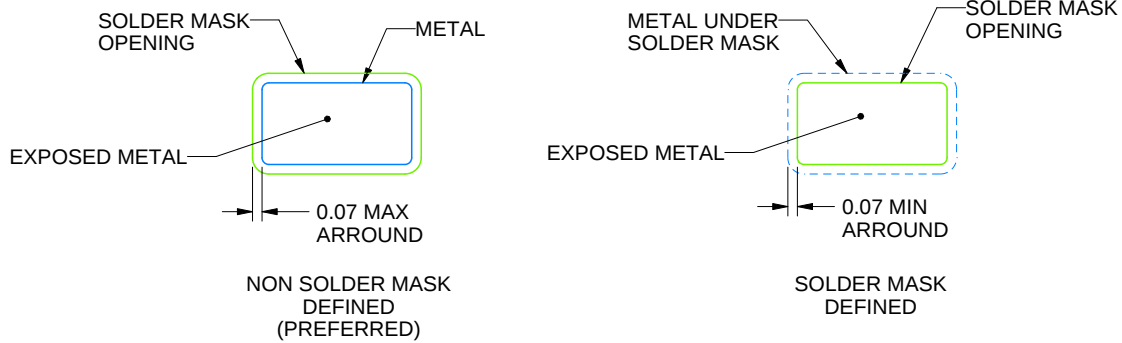
DYF0002A

SOT(SOD-323) - 1 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:25X



SOLDER MASK DETAILS

4228484/C 12/2024

NOTES: (continued)

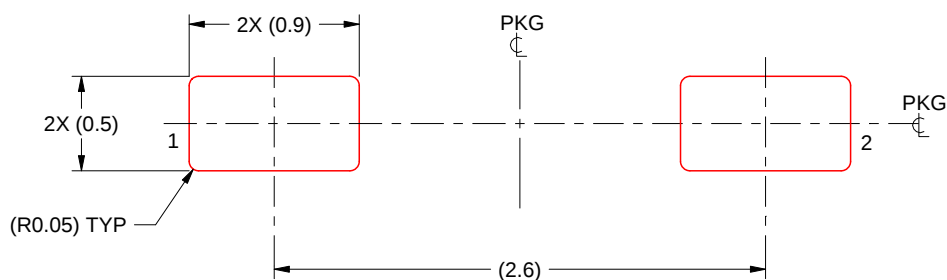
3. Publication IPC-7351 may have alternate designs.
4. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DYF0002A

SOT(SOD-323) - 1 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:25X

4228484/C 12/2024

NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
6. Board assembly site may have different recommendations for stencil design.

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